



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	112
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	96K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 21x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103zgh6

List of figures

Figure 1.	STM32F103xF and STM32F103xG performance line block diagram.	12
Figure 2.	Clock tree	13
Figure 3.	STM32F103xF/G BGA144 ballout	25
Figure 4.	STM32F103xF/G performance line LQFP144 pinout	26
Figure 5.	STM32F103xF/G performance line LQFP100 pinout	27
Figure 6.	STM32F103xF/G performance line LQFP64 pinout	28
Figure 7.	Memory map	39
Figure 8.	Pin loading conditions	40
Figure 9.	Pin input voltage	40
Figure 10.	Power supply scheme	41
Figure 11.	Current consumption measurement scheme	42
Figure 12.	Typical current consumption in Run mode versus frequency (at 3.6 V) - code with data processing running from RAM, peripherals enabled	48
Figure 13.	Typical current consumption in Run mode versus frequency (at 3.6 V)- code with data processing running from RAM, peripherals disabled	48
Figure 14.	Typical current consumption on V _{BAT} with RTC on vs. temperature at different V _{BAT} values	50
Figure 15.	Typical current consumption in Stop mode with regulator in run mode versus temperature at different V _{DD} values	51
Figure 16.	Typical current consumption in Stop mode with regulator in low-power mode versus temperature at different V _{DD} values	52
Figure 17.	Typical current consumption in Standby mode versus temperature at different V _{DD} values	52
Figure 18.	High-speed external clock source AC timing diagram	59
Figure 19.	Low-speed external clock source AC timing diagram	59
Figure 20.	Typical application with an 8 MHz crystal	61
Figure 21.	Typical application with a 32.768 kHz crystal	63
Figure 22.	Asynchronous non-multiplexed SRAM/PSRAM/NOR read waveforms	67
Figure 23.	Asynchronous non-multiplexed SRAM/PSRAM/NOR write waveforms	68
Figure 24.	Asynchronous multiplexed PSRAM/NOR read waveforms	70
Figure 25.	Asynchronous multiplexed PSRAM/NOR write waveforms	71
Figure 26.	Synchronous multiplexed NOR/PSRAM read timings	73
Figure 27.	Synchronous multiplexed PSRAM write timings	75
Figure 28.	Synchronous non-multiplexed NOR/PSRAM read timings	77
Figure 29.	Synchronous non-multiplexed PSRAM write timings	78
Figure 30.	PC Card/CompactFlash controller waveforms for common memory read access	79
Figure 31.	PC Card/CompactFlash controller waveforms for common memory write access	80
Figure 32.	PC Card/CompactFlash controller waveforms for attribute memory read access	81
Figure 33.	PC Card/CompactFlash controller waveforms for attribute memory write access	82
Figure 34.	PC Card/CompactFlash controller waveforms for I/O space read access	82
Figure 35.	PC Card/CompactFlash controller waveforms for I/O space write access	83
Figure 36.	NAND controller waveforms for read access	85
Figure 37.	NAND controller waveforms for write access	85
Figure 38.	NAND controller waveforms for common memory read access	86
Figure 39.	NAND controller waveforms for common memory write access	86
Figure 40.	Standard I/O input characteristics - CMOS port	92

2.3.10 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-16 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example with failure of an indirectly used external oscillator).

Several prescalers allow the configuration of the AHB frequency, the high speed APB (APB2) and the low speed APB (APB1) domains. The maximum frequency of the AHB and the high speed APB domains is 72 MHz. The maximum allowed frequency of the low speed APB domain is 36 MHz. See [Figure 2](#) for details on the clock tree.

2.3.11 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from user Flash: you have an option to boot from any of two memory banks. By default, boot from Flash memory bank 1 is selected. You can choose to boot from Flash memory bank 2 by setting a bit in the option bytes.
- Boot from system memory
- Boot from embedded SRAM

The boot loader is located in system memory. It is used to reprogram the Flash memory by using USART1.

2.3.12 Power supply schemes

- $V_{DD} = 2.0$ to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA} , $V_{DDA} = 2.0$ to 3.6 V: external analog power supplies for ADC, DAC, Reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC or DAC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.
- $V_{BAT} = 1.8$ to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

For more details on how to connect power pins, refer to [Figure 10: Power supply scheme](#).

2.3.13 Power supply supervisor

The device has an integrated power-on reset (POR)/power-down reset (PDR) circuitry. It is always active, and ensures proper operation starting from/down to 2 V. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software. Refer to [Table 12: Embedded reset and power control block characteristics](#) for the values of $V_{POR/PDR}$ and V_{PVD} .

The DMA can be used with the main peripherals: SPI, I²C, USART, general-purpose, basic and advanced-control timers TIMx, DAC, I²S, SDIO and ADC.

2.3.17 RTC (real-time clock) and backup registers

The RTC and the backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are forty-two 16-bit registers used to store 84 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset, and they are not reset when the device wakes up from the Standby mode.

The real-time clock provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and a periodic interrupt. It is clocked by a 32.768 kHz external crystal, resonator or oscillator, the internal low-power RC oscillator or the high-speed external clock divided by 128. The internal low-speed RC has a typical frequency of 40 kHz. The RTC can be calibrated using an external 512 Hz output to compensate for any natural quartz deviation. The RTC features a 32-bit programmable counter for long term measurement using the Compare register to generate an alarm. A 20-bit prescaler is used for the time base clock and is by default configured to generate a time base of 1 second from a clock at 32.768 kHz.

2.3.18 Timers and watchdogs

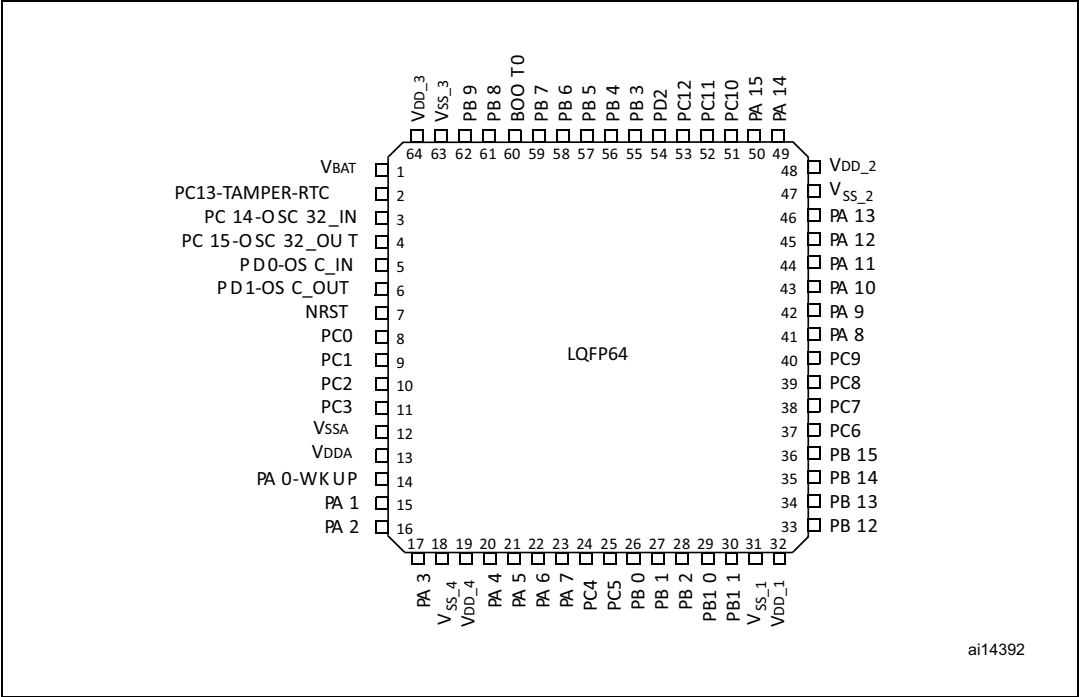
The XL-density STM32F103xF/G performance line devices include up to two advanced-control timers, up to ten general-purpose timers, two basic timers, two watchdog timers and a SysTick timer.

[Table 4](#) compares the features of the advanced-control, general-purpose and basic timers.

Table 4. STM32F103xF and STM32F103xG timer feature comparison

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM1, TIM8	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	Yes
TIM2, TIM3, TIM4, TIM5	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM9, TIM12	16-bit	Up	Any integer between 1 and 65536	No	2	No
TIM10, TIM11 TIM13, TIM14	16-bit	Up	Any integer between 1 and 65536	No	1	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

Figure 6. STM32F103xF/G performance line LQFP64 pinout



1. The above figure shows the package top view.

Table 5. STM32F103xF and STM32F103xG pin definitions (continued)

Pins				Pin name	Type ⁽¹⁾	I / O level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions ⁽⁴⁾	
LFBGA144	LQFP64	LQFP100	LQFP144					Default	Remap
M12	34	52	74	PB13	I/O	FT	PB13	SPI2_SCK / I2S2_CK / USART3_CTS ⁽⁷⁾ / TIM1_CH1N	-
L11	35	53	75	PB14	I/O	FT	PB14	SPI2_MISO / TIM1_CH2N / USART3_RTS ⁽⁷⁾ / TIM12_CH1	-
L12	36	54	76	PB15	I/O	FT	PB15	SPI2_MOSI / I2S2_SD / TIM1_CH3N ⁽⁷⁾ / TIM12_CH2	-
L9	-	55	77	PD8	I/O	FT	PD8	FSMC_D13	USART3_TX
K9	-	56	78	PD9	I/O	FT	PD9	FSMC_D14	USART3_RX
J9	-	57	79	PD10	I/O	FT	PD10	FSMC_D15	USART3_CK
H9	-	58	80	PD11	I/O	FT	PD11	FSMC_A16	USART3_CTS
L10	-	59	81	PD12	I/O	FT	PD12	FSMC_A17	TIM4_CH1 / USART3_RTS
K10	-	60	82	PD13	I/O	FT	PD13	FSMC_A18	TIM4_CH2
G8	-	-	83	V _{SS_8}	S		V _{SS_8}	-	-
F8	-	-	84	V _{DD_8}	S		V _{DD_8}	-	-
K11	-	61	85	PD14	I/O	FT	PD14	FSMC_D0	TIM4_CH3
K12	-	62	86	PD15	I/O	FT	PD15	FSMC_D1	TIM4_CH4
J12	-	-	87	PG2	I/O	FT	PG2	FSMC_A12	-
J11	-	-	88	PG3	I/O	FT	PG3	FSMC_A13	-
J10	-	-	89	PG4	I/O	FT	PG4	FSMC_A14	-
H12	-	-	90	PG5	I/O	FT	PG5	FSMC_A15	-
H11	-	-	91	PG6	I/O	FT	PG6	FSMC_INT2	-
H10	-	-	92	PG7	I/O	FT	PG7	FSMC_INT3	-
G11	-	-	93	PG8	I/O	FT	PG8	-	-
G10	-	-	94	V _{SS_9}	S		V _{SS_9}	-	-
F10	-	-	95	V _{DD_9}	S		V _{DD_9}	-	-
G12	37	63	96	PC6	I/O	FT	PC6	I2S2_MCK / TIM8_CH1 / SDIO_D6	TIM3_CH1
F12	38	64	97	PC7	I/O	FT	PC7	I2S3_MCK / TIM8_CH2 / SDIO_D7	TIM3_CH2
F11	39	65	98	PC8	I/O	FT	PC8	TIM8_CH3 / SDIO_D0	TIM3_CH3

Table 20. Peripheral current consumption⁽¹⁾ (continued)

Peripheral	Current consumption
APB2 (up to 72 MHz)	APB2-Bridge
	2,78
	GPIOA
	7,64
	GPIOB
	7,64
	GPIOC
	7,64
	GIOD
	8,47
	GPIOE
	8,47
	GPIOF
	8,19
	GPIOG
	8,19
	SPI1
	5,14
	USART1
	16,67
	TIM1
	28,47
	TIM8
	24,31
	TIM9
	11,81
	TIM10
	8,47
	TIM11
	8,47
	ADC1 ⁽⁵⁾⁽⁶⁾
	17,68
	ADC2 ⁽⁵⁾⁽⁶⁾
	15,54
	ADC3 ⁽⁵⁾⁽⁶⁾
	16,43

1. $f_{HCLK} = 72 \text{ MHz}$, $f_{APB1} = f_{HCLK}/2$, $f_{APB2} = f_{HCLK}$, default prescaler value for each peripheral.
2. The BusMatrix is automatically active when at least one master peripheral is ON.
3. When the I2S is enabled, a current consumption equal to 0.02 mA must be added.
4. When DAC_OUT1 or DAC_OUT2 is enabled, a current consumption equal to 0.36 mA must be added.
5. Specific conditions for ADC: $f_{HCLK} = 56 \text{ MHz}$, $f_{APB1} = f_{HCLK}/2$, $f_{APB2} = f_{HCLK}$, $f_{ADCCLK} = f_{APB2}/4$. When ADON bit in the ADC_CR2 register is set to 1, a current consumption equal to 0.59 mA must be added.
6. When the ADC is enabled, a current consumption equal to 0.1 mA must be added.

5.3.6 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in [Table 21](#) result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in [Table 10](#).

Figure 27. Synchronous multiplexed PSRAM write timings

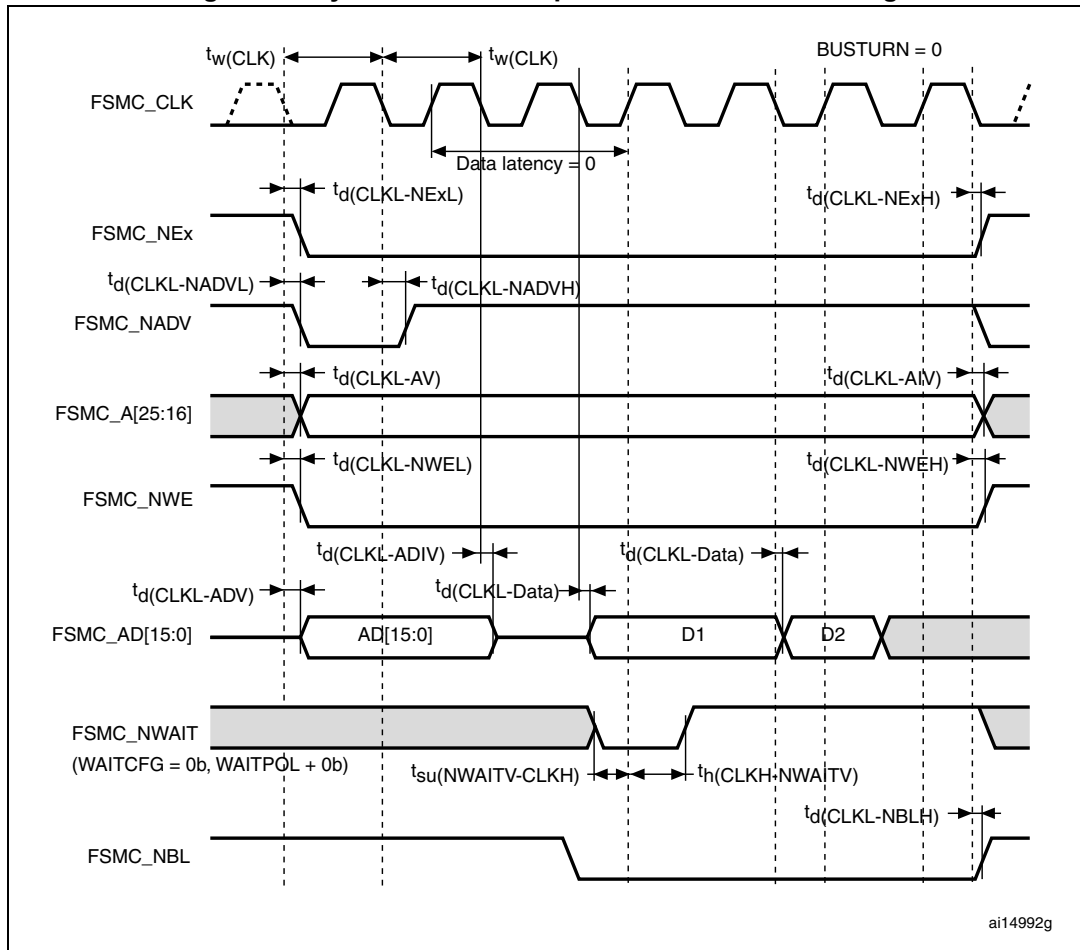
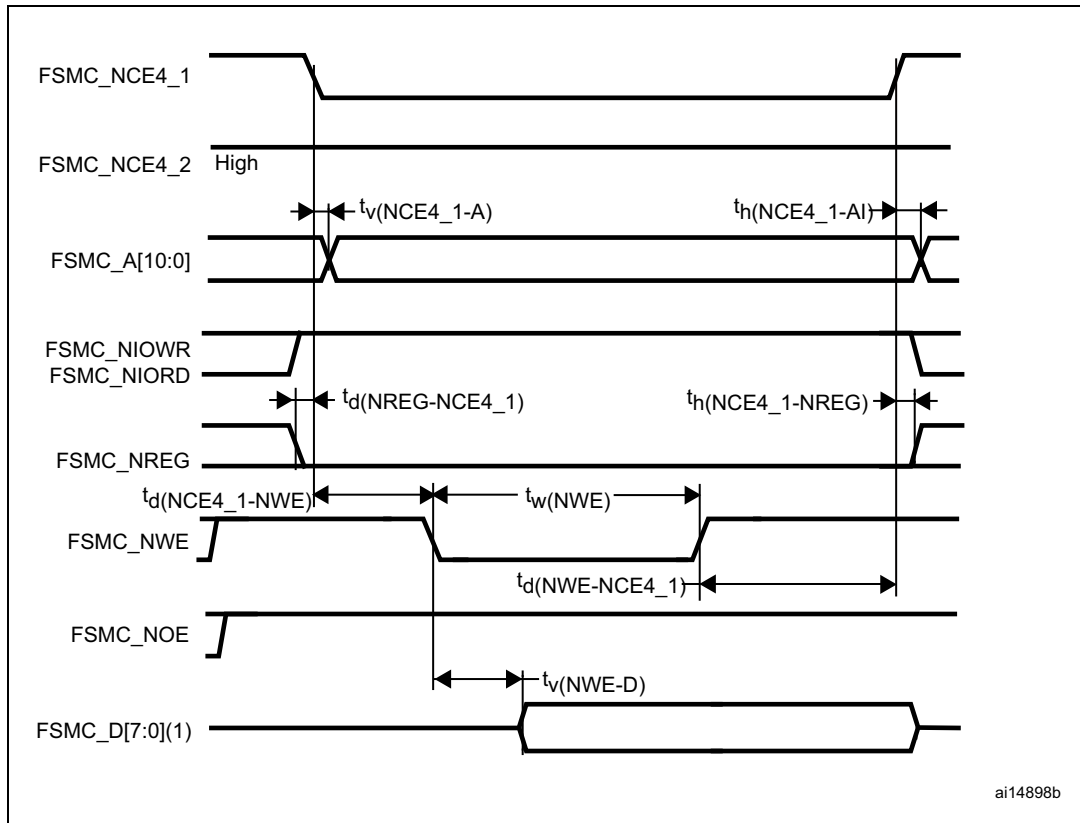


Figure 33. PC Card/CompactFlash controller waveforms for attribute memory write access

1. Only data bits 0...7 are driven (bits 8...15 remains HiZ).

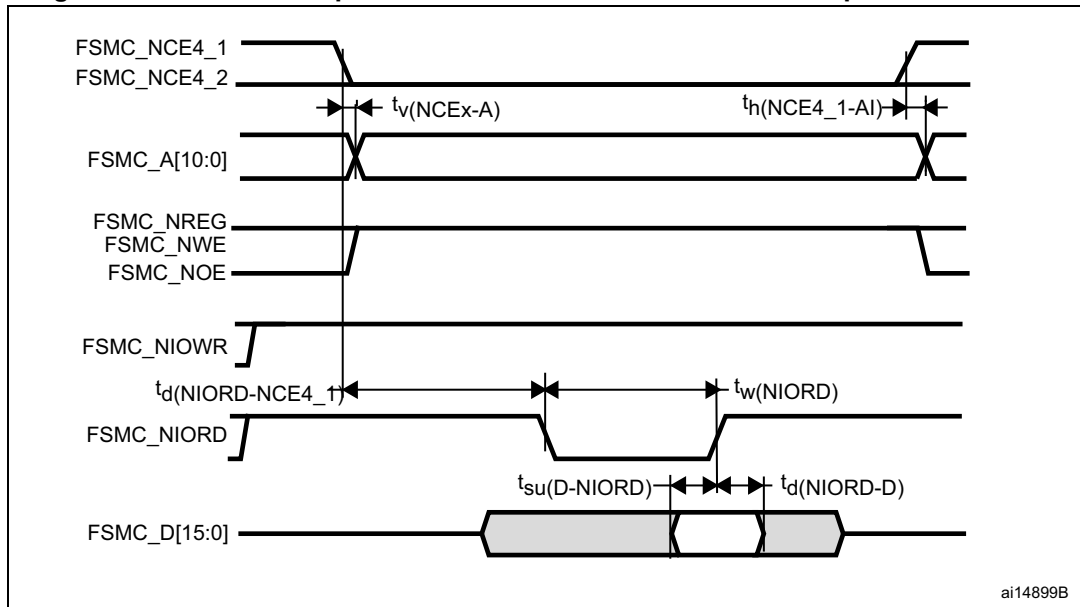
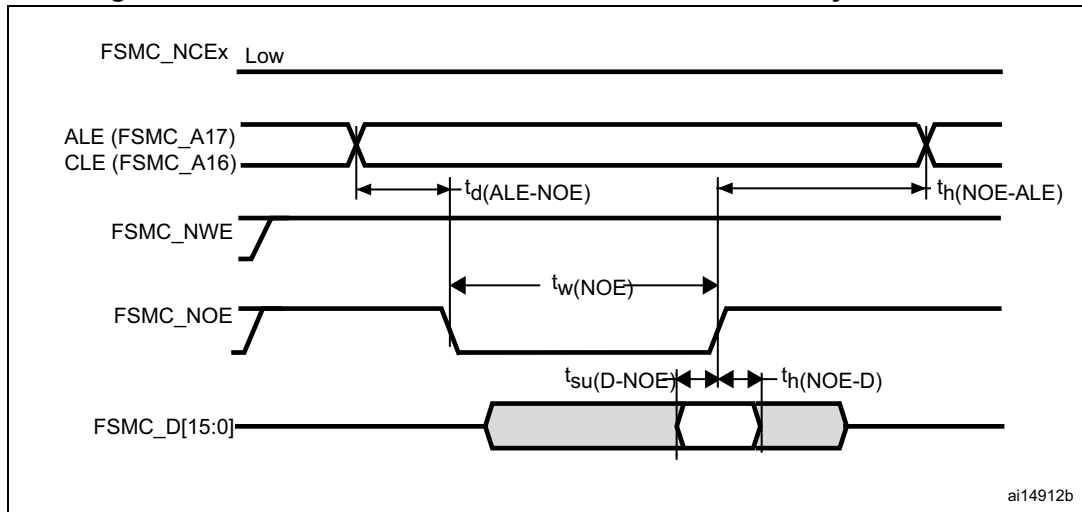
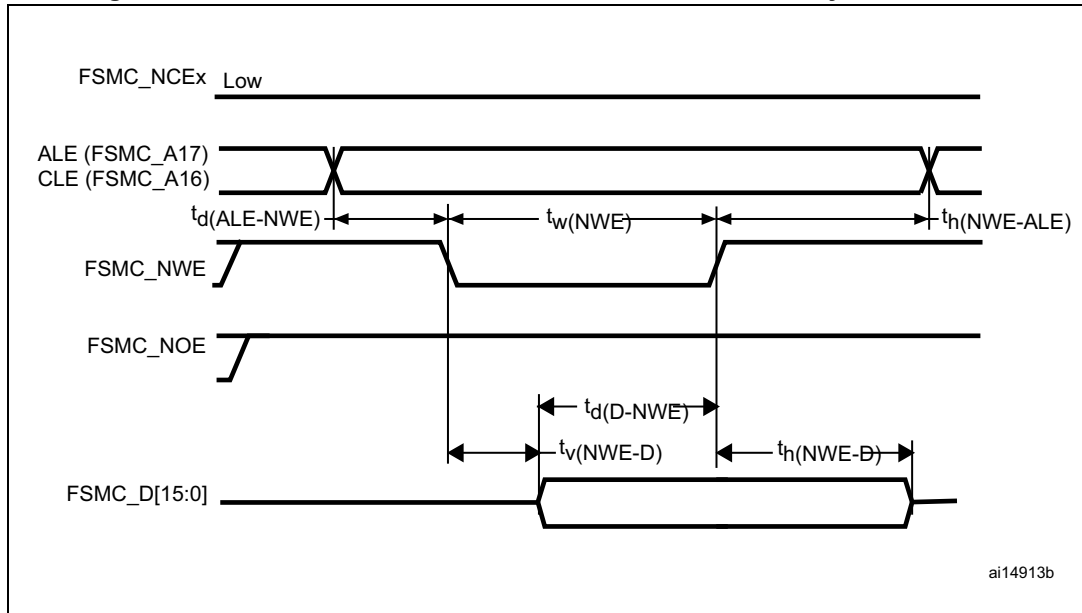
Figure 34. PC Card/CompactFlash controller waveforms for I/O space read access

Figure 38. NAND controller waveforms for common memory read access**Figure 39. NAND controller waveforms for common memory write access****Table 42. Switching characteristics for NAND Flash read cycles⁽¹⁾**

Symbol	Parameter	Min	Max	Unit
$t_{w(NOE)}$	FSMC_NOE low width	$3t_{HCLK} - 1$	$3t_{HCLK} + 1$	ns
$t_{su(D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	13	-	ns
$t_{h(NOE-D)}$	FSMC_D[15:0] valid data after FSMC_NOE high	0	-	ns
$t_{d(ALE-NOE)}$	FSMC_ALE valid before FSMC_NOE low	-	$2t_{HCLK}$	ns
$t_{h(NOE-ALE)}$	FSMC_NWE high to FSMC_ALE invalid	$2t_{HCLK}$	-	ns

1. $C_L = 15$ pF.

Table 47. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	$T_A = +105\text{ }^{\circ}\text{C}$ conforming to JESD78A	II level A

5.3.13 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard, 3 V-capable I/O pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error above a certain limit (>5 LSB TUE), out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation).

The test results are given in [Table 48](#)

Table 48. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on OSC_IN32, OSC_OUT32, PA4, PA5, PC13	-0	+0	mA
	Injected current on all FT pins	-5	+0	
	Injected current on any other pin	-5	+5	

Figure 40. Standard I/O input characteristics - CMOS port

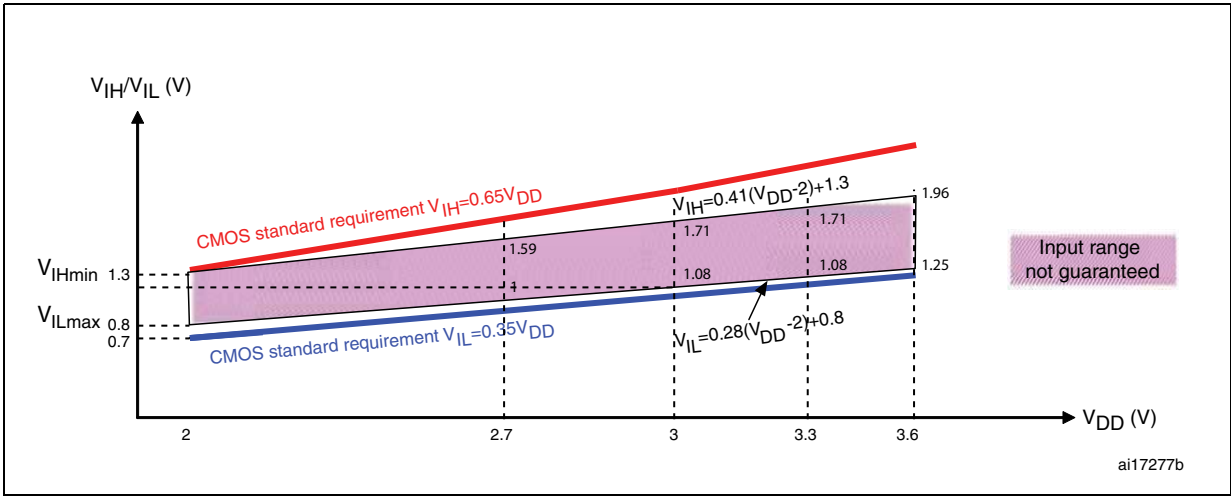


Figure 41. Standard I/O input characteristics - TTL port

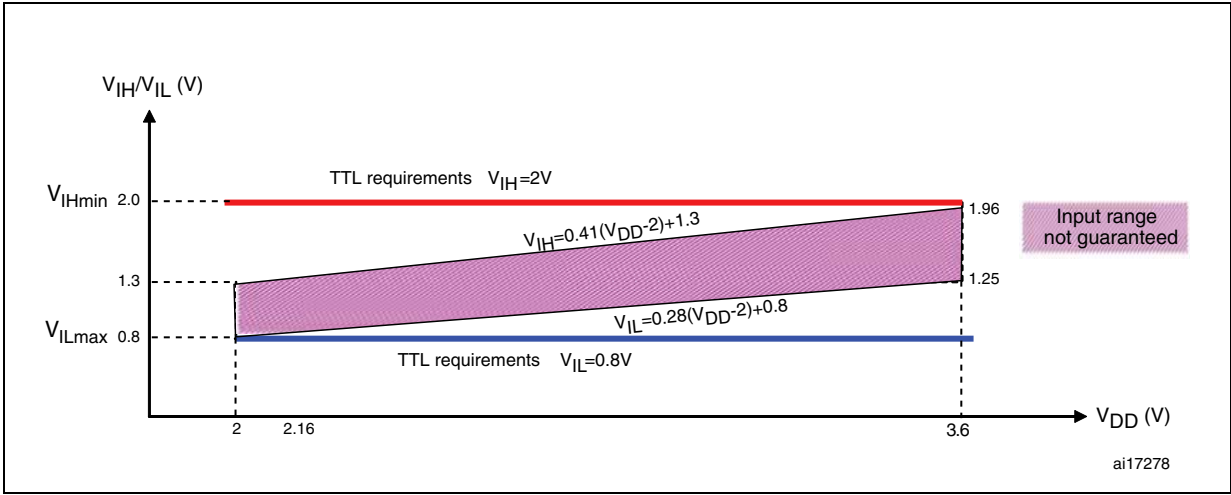
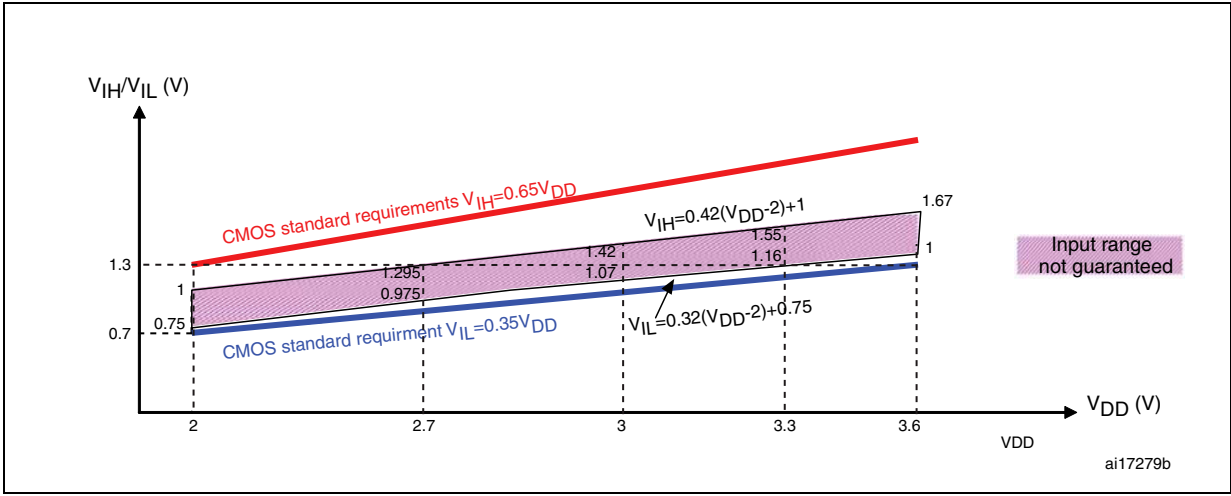


Figure 42. 5 V tolerant I/O input characteristics - CMOS port



I²S - SPI characteristics

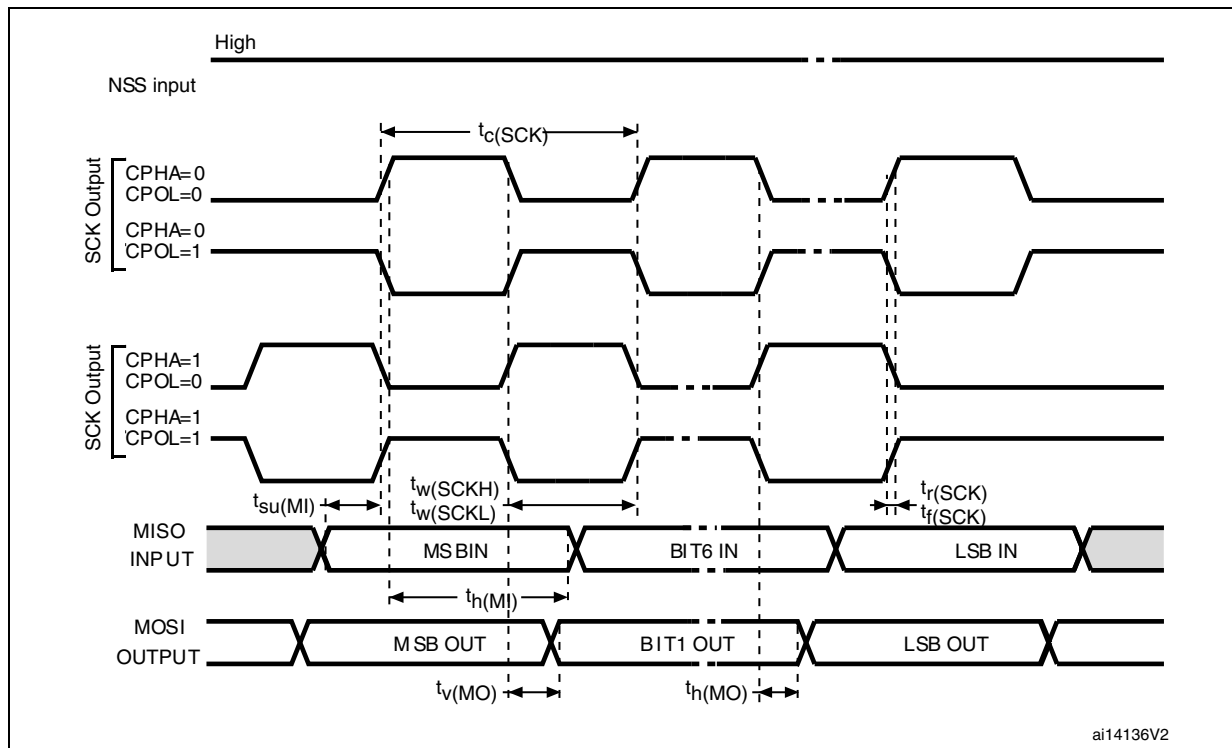
Unless otherwise specified, the parameters given in [Table 56](#) for SPI or in [Table 57](#) for I²S are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 10](#).

Refer to [Section 5.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI and WS, CK, SD for I²S).

Table 56. SPI characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{SCK} $1/t_c(SCK)$	SPI clock frequency	Master mode	-	18	MHz
		Slave mode	-	18	
$t_r(SCK)$ $t_f(SCK)$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	8	ns
DuCy(SCK)	SPI slave input clock duty cycle	Slave mode	30	70	%
$t_{su(NSS)}^{(1)}$	NSS setup time	Slave mode	$4t_{PCLK}$	-	ns
$t_{h(NSS)}^{(1)}$	NSS hold time	Slave mode	$2t_{PCLK}$	-	
$t_{w(SCKH)}^{(1)}$ $t_{w(SCKL)}^{(1)}$	SCK high and low time	Master mode, $f_{PCLK} = 36$ MHz, presc = 4	50	60	
$t_{su(MI)}^{(1)}$ $t_{su(SI)}^{(1)}$	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}^{(1)}$ $t_{h(SI)}^{(1)}$	Data input hold time	Master mode	5	-	
		Slave mode	4	-	
$t_{a(SO)}^{(1)(2)}$	Data output access time	Slave mode, $f_{PCLK} = 20$ MHz	0	$3t_{PCLK}$	
$t_{dis(SO)}^{(1)(3)}$	Data output disable time	Slave mode	2	10	
$t_{v(SO)}^{(1)}$	Data output valid time	Slave mode (after enable edge)	-	25	
$t_{v(MO)}^{(1)}$	Data output valid time	Master mode (after enable edge)	-	5	
$t_{h(SO)}^{(1)}$ $t_{h(MO)}^{(1)}$	Data output hold time	Slave mode (after enable edge)	15	-	
		Master mode (after enable edge)	2	-	

1. Guaranteed by characterization results, not tested in production.
2. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
3. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z

Figure 49. SPI timing diagram - master mode⁽¹⁾

1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

- Guaranteed by design, not tested in production.
- V_{REF+} can be internally connected to V_{DDA} and V_{REF-} can be internally connected to V_{SSA} , depending on the package. Refer to [Section 3: Pinouts and pin descriptions](#) for further details.
- For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in [Table 62](#).

Equation 1: R_{AIN} max formula

$$R_{AIN} < \frac{T_s}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above ([Equation 1](#)) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. Here $N = 12$ (from 12-bit resolution).

Table 63. R_{AIN} max for $f_{ADC} = 14$ MHz⁽¹⁾

T_s (cycles)	t_s (μs)	R_{AIN} max (kΩ)
1.5	0.11	0.4
7.5	0.54	5.9
13.5	0.96	11.4
28.5	2.04	25.2
41.5	2.96	37.2
55.5	3.96	50
71.5	5.11	NA
239.5	17.1	NA

- Guaranteed by design, not tested in production.

Table 64. ADC accuracy - limited test conditions⁽¹⁾⁽²⁾

Symbol	Parameter	Test conditions	Typ	Max ⁽³⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56$ MHz, $f_{ADC} = 14$ MHz, $R_{AIN} < 10$ kΩ, $V_{DDA} = 3$ V to 3.6 V $T_A = 25$ °C Measurements made after ADC calibration $V_{REF+} = V_{DDA}$	±1.3	±2	LSB
EO	Offset error		±1	±1.5	
EG	Gain error		±0.5	±1.5	
ED	Differential linearity error		±0.7	±1	
EL	Integral linearity error		±0.8	±1.5	

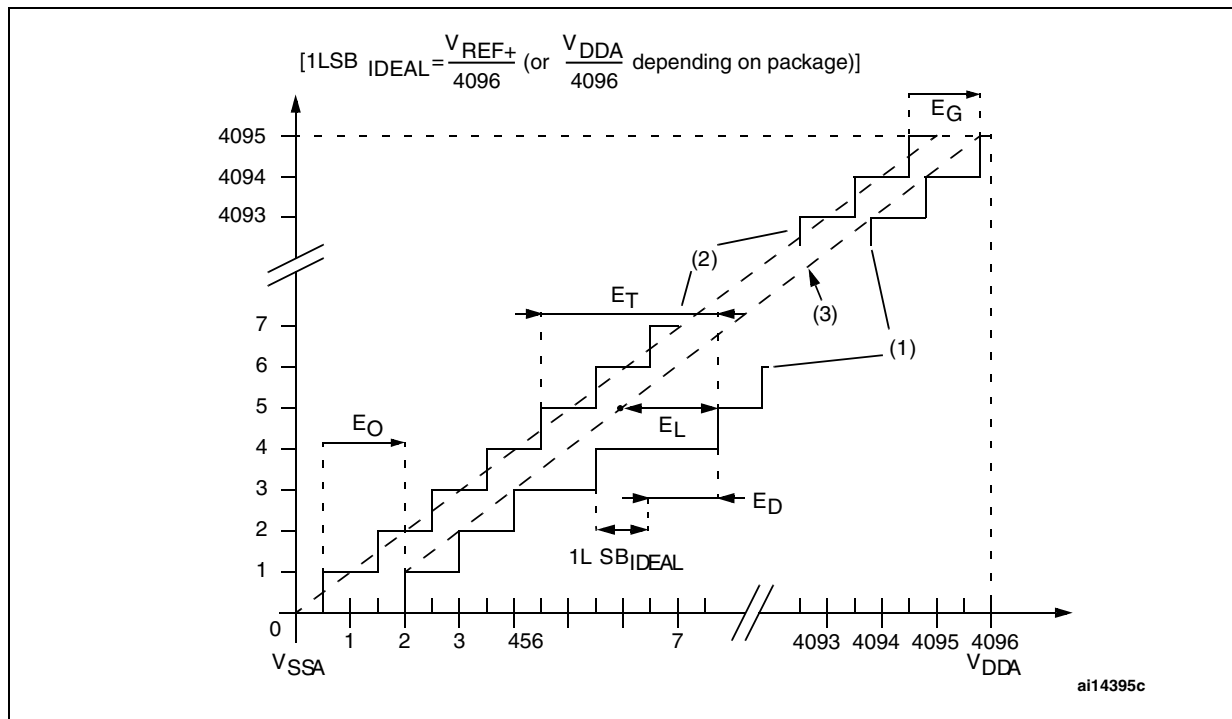
- ADC DC accuracy values are measured after internal calibration.
- ADC Accuracy vs. Negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 5.3.14](#) does not affect the ADC accuracy.
- Guaranteed by characterization results, not tested in production.

Table 65. ADC accuracy^{(1) (2)(3)}

Symbol	Parameter	Test conditions	Typ	Max ⁽⁴⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 14 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$, $V_{DDA} = 2.4 \text{ V to } 3.6 \text{ V}$ Measurements made after ADC calibration	± 2	± 5	LSB
EO	Offset error		± 1.5	± 2.5	
EG	Gain error		± 1.5	± 3	
ED	Differential linearity error		± 1	± 2	
EL	Integral linearity error		± 1.5	± 3	

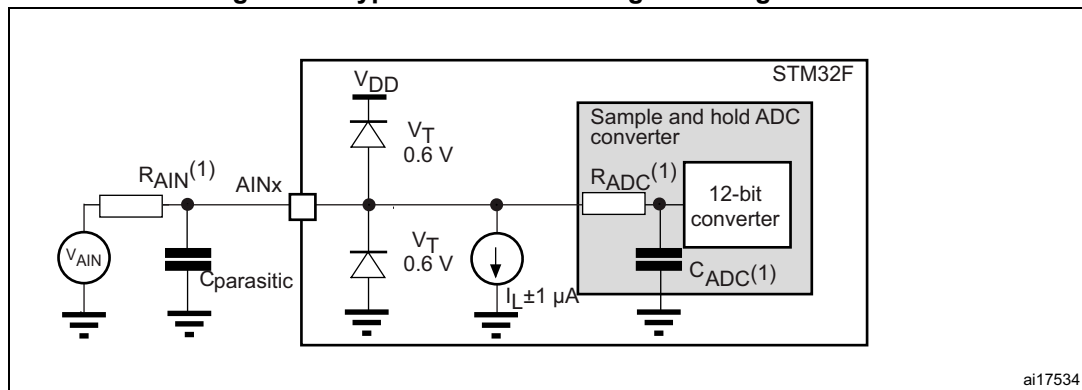
1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD} , frequency, V_{REF} and temperature ranges.
3. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 5.3.14](#) does not affect the ADC accuracy.
4. Preliminary values.

Figure 55. ADC accuracy characteristics



1. Example of an actual transfer curve.
2. Ideal transfer curve.
3. End point correlation line.
4. ET = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
 EO = Offset Error: deviation between the first actual transition and the first ideal one.
 EG = Gain Error: deviation between the last ideal transition and the last actual one.
 ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
 EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

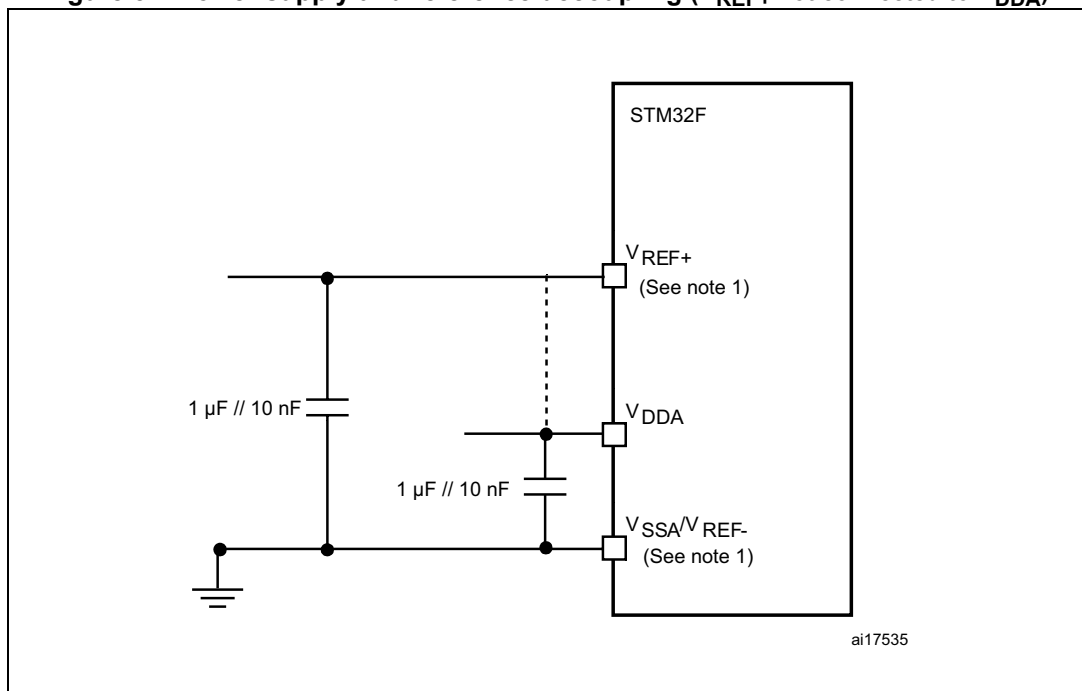
Figure 56. Typical connection diagram using the ADC



1. Refer to [Table 62](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 57](#) or [Figure 58](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 57. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

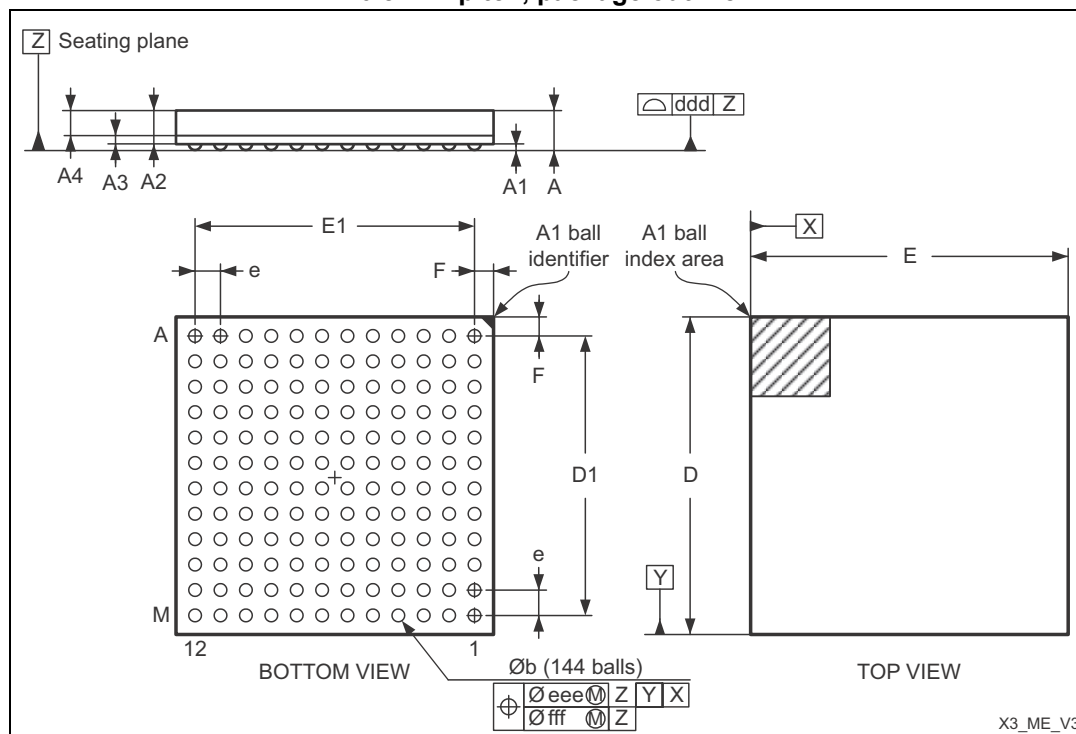
1. V_{REF+} and V_{REF-} inputs are available only on 100-pin packages.

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

6.1 LFBGA144 package information

Figure 60. LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package outline

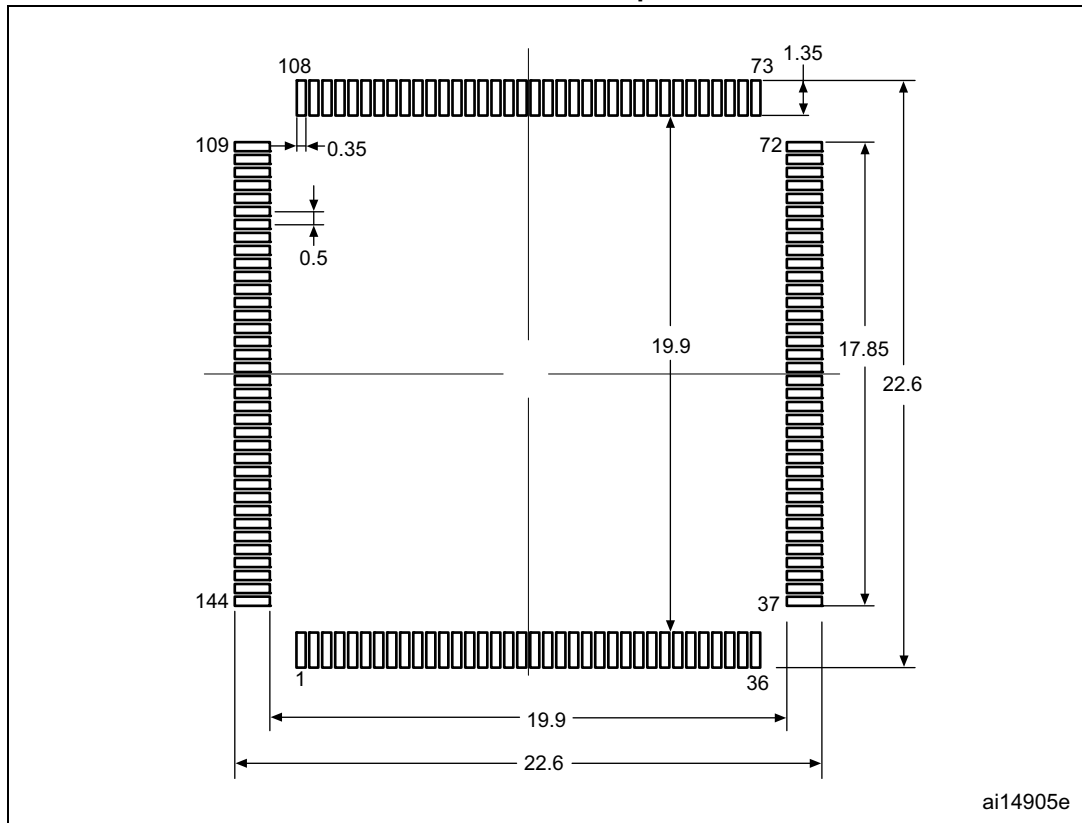


1. Drawing is not to scale.

Table 68. LFBGA144 – 144-ball low profile fine pitch ball grid array, 10 x 10 mm, 0.8 mm pitch, package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Typ	Min	Max
A ⁽²⁾	-	-	1.700			0.0669
A1	0.210	-	-	0.0083		
A2	-	1.060	-		0.0417	
A3		0.026			0.0010	
A4	-	0.800	-	-	0.0315	-
b	0.350	0.400	0.450	0.0138	0.0157	0.0177
D	9.850	10.000	10.150	0.3878	0.3937	0.3996
D1	-	8.800	-	-	0.3465	-
E	9.850	10.000	10.150	0.3878	0.3937	0.3996
E1	-	8.800	-	-	0.3465	-
e	-	0.800	-	-	0.0315	-
F	-	0.600	-	-	0.0236	-
ddd	-	-	0.100	-	-	0.0039

Figure 63. LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Table 74. Document revision history

Date	Revision	Changes
15-May-2015	4	<p>Added document status on first page.</p> <p>Replace DAC1_OUT/DAC2_OUT by DAC_OUT1/DAC_OUT2, and updated TIM5 in Figure 1: STM32F103xF and STM32F103xG performance line block diagram on page 12.</p> <p>Replaced USBDP/USBDM by USB_DP/USB_DM in the whole document.</p> <p>Updated notes related to electrical values guaranteed by characterization results.</p> <p>Updated Table 20: Peripheral current consumption.</p> <p>Updated Table 36: Synchronous multiplexed NOR/PSRAM read timings to Table 39: Synchronous non-multiplexed PSRAM write timings(added FSMC_NWAIT timings). Updated Figure 26: Synchronous multiplexed NOR/PSRAM read timings on page 73 and Figure 28: Synchronous non-multiplexed NOR/PSRAM read timings on page 77 and Figure 35: PC Card/CompactFlash controller waveforms for I/O space write access on page 83.</p> <p>Updated CDM class in Table 46: ESD absolute maximum ratings.</p> <p>Updated Figure 44: I/O AC characteristics definition on page 96 and Figure 45: Recommended NRST pin protection on page 97.</p> <p>Updated Figure 49: SPI timing diagram - master mode⁽¹⁾ on page 96.</p> <p>Modified note 3 in Table 56: SPI characteristics.</p> <p>Section : I2C interface characteristics: Updated introduction, updated Table 54: I²C characteristics and Figure 46: I²C bus AC waveforms and measurement circuit on page 99.</p> <p>Modified note 2 in Table 64: ADC accuracy - limited test conditions, Figure 55: ADC accuracy characteristics on page 110 and Figure 56: Typical connection diagram using the ADC on page 111. Updated Figure 57: Power supply and reference decoupling (V_{REF+} not connected to V_{DDA}) on page 111 and Figure 58: Power supply and reference decoupling (V_{REF+} connected to V_{DDA}) on page 112.</p> <p>Updated I_{DDA} description and Offset comment in Table 66: DAC characteristics.</p> <p>Updated Section 6.1: LFBGA144 package information and added Section : Device marking for LFBGA144 package.</p> <p>Updated Section 6.2: LQFP144 package information and added Section : Device marking for LQFP144 package.</p> <p>Updated Section 6.3: LQFP100 package information and added Section : Device marking for LQFP100 package.</p> <p>Updated Section 6.4: LQFP64 package information and added Section : Device marking for LQFP64 package.</p>